

Achieving accuracy in charge carrier mobility modelling in silicon

Mnatsakanov, T.T.; Gresserov, B.N.; Pomortseva, L.I. Automation, simulation & measurement : 3rd biennial conference : Tallinn, Estonia, October 7-11, 1991. Section S, Simulation = Automatiseerimine, modelleerimine ja mõõtmine : 3. rahvusvaheline konverents / Tallinna Tehnikaülikool 1992 / p. 89-94: ill https://www.ester.ee/record=b1064031*est

AFM and SEM investigations of ion beam synthesized Mg₂Si precipitates in Si substrates

Angelov, Christo; **Mikli, Valdek**; Amov, Blagoj; Goranova, E. Journal of optoelectronics and advanced materials 2005 / 1, p. 369-373 https://old.joam.inoe.ro/arhiva/pdf7_1/Angelov3.pdf

Analyses of frequency dependencies of Q factor for planar inductors on silicon

Jankovskis, Janis; Yurshevich, Valentins; Rankis, Gunars BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 231-234

Band gap engineering by cationic substitution in Sn(Zr_{1-x}Ti_x)Se₃ alloy for bottom sub-cell application in solar cells

Kondrotas, Rokas; Pakstas, Vidas; Franckevicius, Marius; Suchodolskis, Arturas; Tumenas, Saulius; Jasinskas, Vidmantas; Juskenas, Remigijus; Krotkus, Arunas; **Muska, Katri; Kauk-Kuusik, Marit** Journal of materials chemistry A 2023 / p. 26488–26498 : ill <https://doi.org/10.1039/D3TA05550G> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Comparative ellipsometric and ion beam analytical studies on ion beam crystallized silicon implanted with Zn and Pb ions

Lohner, Tivador; Angelov, Christo; **Mikli, Valdek** Thin solid films 2008 / 22, p. 8009-8012 <https://www.sciencedirect.com/science/article/pii/S0040609008003660>

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC

Velmre, Enn; Udal, Andres Physica scripta 1999 / p. 193-197 : ill <https://ui.adsabs.harvard.edu/abs/1999PhST...79..193V/abstract> <https://doi.org/10.1238/Physica.Topical.079a00193>

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC

Velmre, Enn; Udal, Andres 18th Nordic Semiconductor Meeting, Linköping, June 7-10, 1998 : abstracts 1998 / p. F-88: ill <https://iopscience.iop.org/article/10.1238/Physica.Topical.079a00193>

Correlation between the UV-reflectance spectra and the structure of poly-Si films obtained by aluminium induced crystallization

Dimova-Malinovska, D.; Angelov, O.; Sendova-Vassileva, M.; **Mikli, Valdek** Journal of optoelectronics and advanced materials 2009 / 9, p. 1079-1085 https://www.researchgate.net/publication/288122478_Correlation_between_the_UV-reflectance_spectra_and_the_structure_of_poly-Si_films_obtained_by_Aluminium_Induced_Crystallization

A double-emitter silicon differential strain sensitive transistor with an accelerating field in its base

Babichev, G.G.; Kozlovskii, S.I.; Romanov, V.A.; Sharan, N.N. BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 263-264: ill

Eesti teadlased loovad tuleviku päikesepaneeli

Grossberg-Kuusk, Maarja postimees.ee 2025 / lk. 6 <https://arvamus.postimees.ee/8276259/maarja-grossberg-kuusk-eesti-teadlased-loovad-tuleviku-paikesepaneeli> <https://dea.digar.ee/article/postimees/2025/06/28/7.4>

Effect of calcium to silicon ratio on the microstructure of hydrated calcium silicate gels prepared under medium alkalinity

Ba, Haojing; Li, Jiajie; Ni, Wen; Li, Ying; Ju, Yongjian; Zhao, Ben; Wen, Guoping; **Hitch, Michael William** Construction and building materials 2023 / art. 131240, 11 p.: ill <https://doi.org/10.1016/j.conbuildmat.2023.131240>

Effect of silica precursor on the synthesis of Zn₂SiO₄-based material

Rojas Hernandez, Rocio Estefania; Hussainova, Irina; Necib, Jallouli Proceedings of the Estonian Academy of Sciences 2025 / p. 217-221 <https://doi.org/10.3176/proc.2025.2.24>

Electrochemical deposition of thin polypyrrole films on silicon substrates

Intelmann, Carl Matthias; **Sõritski, Vitali**; Tsankov, Dimiter; Hinrichs, Karsten; Rappich, Jörg 5th ISE Spring Meeting : Dublin (Ireland), 01.-04.05.07 2007 / ? p

Electrochemically deposited ultrathin polypyrrole films on silicon

Intelmann, Carl Matthias; **Sõritski, Vitali**; Tsankov, Dimiter; Hinrichs, Karsten; Rappich, Jörg GDCh (German Chemical Society) - YoungChemists : Spring Symposium 2007 : Chemnitz (Germany), 22.-24.03.07 2007 / ? p

From virtual characterization to test-chips : DFM analysis through pattern enumeration

Martins, Mayler G.A.; **Pagliarini, Samuel Nascimento**; Isgenc, Mehmet Meric; Pileggi, Larry IEEE transactions on computer-aided design of integrated circuits and systems 2020 / p. 520-532 <https://doi.org/10.1109/TCAD.2018.2889772>

High phonon-drag thermoelectric efficiency of SiC at low temperatures

Velmre, Enn; Udal, Andres; Grivickas, Vytautas Final program of the 10th International Conference on SiC and Related Materials :

ICSCRM'2003 : Lyon, France, Oct. 5-10, 2003 / p. ThP4-13 https://www.researchgate.net/publication/240834700_High_Phonon-Drift_Thermoelectric_Efficiency_of_SiC_at_Low_Temperatures

Hydrogen interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 <https://www.scientific.net/SSP.131-133.345>

Impurity interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A. Materials science and engineering : B 2006 / p. 222-226 : ill <https://www.sciencedirect.com/science/article/pii/S0921510706004375>

Influence of differently formed interfacial aluminium oxide on the structural properties of poly-Si films prepared by aluminium induced crystallisation

Dimova-Malinovska, D.; Nichev, H.; Angelov, O.; Sendova-Vassileva, M.; Sendova, M.; **Mikli, Valdek** Journal of optoelectronics and advanced materials 2007 / 2, p. 359-362

Influence of excitonic scattering on charge carrier ambipolar diffusion in silicon

Udal, Andres; Velme, Enn ESSDERC'97 : proceedings of the 27th European Solid-State Device Research Conference, Stuttgart, Germany, 22-24 September 1997 / p. 212-215: ill <https://ieeexplore.ieee.org/stamp/stamp.jsp?tp=&arnumber=1503333>

Interaction between point defects in the Si-Si=2 system

Kropman, Daniel; Kärner, T.; Samoson, Ago; Heinmaa, I.; **Melikov, Enn** Nuclear instruments & methods in physics research. Section B 2002 / p. 78-82 <https://www.sciencedirect.com/science/article/pii/S0168583X0100862X>

Interaction between point defects in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Samoson, Ago; Heidmaa, I.; Ugaste, Ülo; **Melikov, Enn** Defect and Diffusion Forum 2001 / p. 1737-1744 <https://www.sciencedirect.com/science/article/abs/pii/S0168583X0100862X>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

Interaktsioon punktdefektide ja lisandite vahel süsteemis Si-SiO₂ ja nende mõju piirpinna omadustele : [ettekande sisukokkuvõte]

Kropman, Daniel; Kärner, T.; Heinmaa, I. Eesti Füüsika Seltsi aastaraamat 2008 2009 / lk. 119-120

Jaan Raik: Computers must undergo a revolution in order to continue their rapid development

Raik, Jaan Estonian Centre of Excellence in ICT Research 2021 / p. 43-47 : ill <http://www.digar.ee/id/nlib-digar:634779>
https://www.ester.ee/record=b5456158*est

Jaan Raik: kiibidisain aitaks saada Eestil jõukaks tehnoloogiamaks

Maidla, Margus novaator.err.ee 2023

Kassikuld võib osutuda elektroonikatööstuses kullast kallimaks

Kristmann, Katrin novaator.err.ee 2024 [Kassikuld võib osutuda elektroonikatööstuses kullast kallimaks](#)

Keemia tee klaasist ränisse : tänavune Nobeli keemiaauhind seab õigluse jalule keemiateoreetikute ja arvutikeemikute hulgas

Strandberg, Marek Sirp 2013 / lk. 26 <https://www.sirp.ee/s1-artiklid/c21-teadus/2013-10-17-20-15-58-2/>

Kleenukesed päikeseelemendid aitaks vältida ränipaneele ootavat kriisi

Sibinski, Maciej novaator.err.ee 2024 [Kleenukesed päikeseelemendid aitaks vältida ränipaneele ootavat kriisi](#)

Modeling of charge carrier non-isothermal transport parameters in silicon

Velme, Enn; Udal, Andres BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 71-74: ill

Modelling of charge carrier non-isothermal transport in silicon and silicon carbide

Velme, Enn; Udal, Andres Proceedings of the Estonian Academy of Sciences. Engineering 2000 / p. 144-154 : ill
https://artiklid.elnet.ee/record=b1004044*est

Modular synthesis of (Borylmethyl)silanes through orthogonal functionalization of a carbon atom

Chowdhury, Rajdip; **Elek, Gábor Zoltán**; Meana-Baamonde, B.; Mendoza, Abraham Organic letters 2023 / p. 1935-1940 : ill <https://doi.org/10.1021/acs.orglett.3c00474> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Must rāni tõi helged lootused

Krustok, Jüri Eesti Päevaleht 2000 / 19. veebr., lk. 23 https://artiklid.elnet.ee/record=b1637055*est

Point defects interaction with extended defects and impurities and its influence on the Si-SiO₂ system properties

Kropman, Daniel; Arbu, Uno; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit**; Heinmaa, I.; **Samoson, Ago**; Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill

[https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO₂ System Properties](https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO2_System_Properties)

Point defects interaction with extended defects in the Si-SiO₂ system [Electronic resource]

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Proceedings IVC-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM]

[https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO₂ System Properties](https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO2_System_Properties)

Porphyrin-based hybrid nanohelices : cooperative effect between molecular and supramolecular chirality on amplified optical activity

Anfar, Zakaria; Kuppan, Balamurugan; Scalabre, Antoine; Nag, Rahul; Pouget, Emilie; Nlate, Sylvain; Magna, Gabriele; Di Filippo, Ilaria; Monti, Donato; Naitana, Mario L.; Stefanelli, Manuela; **Nikonovich, Tatsiana**; **Borovkov, Victor**; **Aav, Riina**; Paolesse, Roberto; Oda, Reiko The journal of physical chemistry B 2024 / p. 1550-1556 <https://doi.org/10.1021/acs.jpcc.3c07153> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Predictable quantum efficient detector. I, Photodiodes and predicted responsivity

Sildoja, Meelis; Manoocheri, Farshid; Merimaa, Mikko; Ikonen, Erkki; Müller, Ingmar; Werner, Lutz; Gran, Jarle; **Kübarsepp, Toomas**; Smid, Marek; Rastello, Maria Luisa Metrologia 2013 / p. 385-394 : ill <https://doi.org/10.1088/0026-1394/50/4/385>

<https://cris.vtt.fi/en/publications/predictable-quantum-efficient-detector-i-photodiodes-and-predicted-responsivity> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Production of silicon free master alloys in Estonia

Gorkunov, Valeri; **Munter, Rein** Scientific proceedings of Riga Technical University. 1. [series], Material science and applied chemistry 2007 / p. 111-121

Päikeseenergeetika tulevikku kujundavad kilepinnad ja tandempaneelid

Piir, Rait novaator.err.ee 2023 [Päikeseenergeetika tulevikku kujundavad kilepinnad ja tandempaneelid](#)

Rapid prototyping of silicon structures by aid of laser and abrasive-jet machining

Kruusing, Arvi; Leppävuori, Seppo; Uusimäki, Antti; Uusimäki, M. Design, Test and Microfabrication of MEMS and MOEMS : 30 March-1 April, 1999, Paris, France 1999 / p. 870-878 : ill <https://opticalengineering.spiedigitallibrary.org/conference-proceedings-of-spie/3680/0000/Rapid-prototyping-of-silicon-structures-by-aid-of-laser-and/10.1117/12.341285.full>

Recombination behaviour at the ultra-thin polypyrrole film/silicon interface investigated by in-situ pulsed photoluminescence

Intelmann, Carl Matthias; Hinrichs, Karsten; **Sörtski, Vitali**; Yang, Florent; Rappich, Jörg Japanese journal of applied physics 2008 / 2, p. 554-557 <https://iopscience.iop.org/article/10.1143/JJAP.47.554>

Relationships between essential and non-essential elements in plants with different nutritional strategies and silicon absorption capacities : [manuscript]

Monei, Nthathi Lilian; Benyr, V.; Heilmeyer, Hermann; **Hitch, Michael William**; Wiche, Oliver The international journal of environment & health 2023

Review of - SiC wide-bandgap heterostructure properties as an alternate semiconductor material

Patankar, Udayan Sunil; Rajput Priti, J.; **Koel, Ants**; Nitaware, V.N. International Conference on Inventive Research in Material Science and Technology, ICIRMCT 2018 : March 23-24, 2018 2018 / art. 020011 <https://doi.org/10.1063/1.5038690> [Conference proceedings at Scopus](#) [Article at Scopus](#) [Article at WOS](#)

Selective laser melting of commercially pure silicon

Lai, Zhouyi; Guo, Ting; Zhang, Shengting; Kollo, Lauri; Attar, Hooyar; Wang, Zhi; **Prashanth, Konda Gokuldoss** Journal Wuhan University of Technology, Materials Science Edition 2022 / p. 1155 - 1165 <https://doi.org/10.1007/s11595-022-2647-3> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Silica granulates in concrete - dispersion and durability aspects

Lagerblad, Björn; **Utkin, Pjotr** 1993 https://www.ester.ee/record=b1025989*est

Szilícium planar technologiai eljárás számítógépes stimulációja

Rang, Toomas; Tamay, K.; Masszi, F. Finommechanika, mikrotechnika: az Optikai, Akusztikai és Filmtechnikai Egyesület, a Híradástechnikai Tudományos Egyesület és a Méréstechnikai és Automatizálási Tudományos Egyesület lapja 1979 / p. 257-260

Strain relaxation mechanism in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Öpik, Andres; Lott, Kalju; Volobujeva, Olga; Kämer, T.; Heinmaa, I.; Laas, Tõnu; Medvid, A. Physica B : condensed matter 2009 / 23/24, p. 5153-5155 : ill

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Seeman, Viktor; Dolgov, Sergei; Heinmaa, Ivo; Medvid, Artur Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 790 - 792 <https://doi.org/10.1002/pssc.201600051> [Journal metrics at Scopus](#) [Article at Scopus](#) [Article at WOS](#)

Study of ion implanted Fe depth distribution in Si after pulsed ion beam treatment

Angelov, Christo; Georgiev, S.; Amov, Blagoj; Goranova, E.; **Mikli, Valdek**; Dezs, I.; Kotai, E. Journal of optoelectronics and advanced materials 2007 / 2, p. 307-310
https://www.researchgate.net/publication/289186791_Study_of_the_ion_implanted_Fe_depth_distribution_in_Si_after_pulsed_ion_beam_treatment

Technonomics of manufacturing of silicon microsystems on WSI

Bubennikov, Alexander N.; Bubennikov, Alexander A. BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 29-32: ill

The role of silicon in the hot dip galvanizing process

Sepper, Sirl; Peetsalu, Priidu; Kulu, Priit; Saarna, Mart; Mikli, Valdek Proceedings of the Estonian Academy of Sciences 2016 / p. 159-165 : ill https://artiklid.elnet.ee/record=b2768226*est <https://doi.org/10.3176/proc.2016.2.11> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Ursache und Wirkungsweise der Alkalireaktion in den aus estnischem Portlandölschieferzement hergestellten Betonen

Kikas, Verner; Ojaste, Kalju; Raado, Lembi-Merike ZKG International = Zement, Kalk, Gips international 1999 / 2, S. 106-111

Use of atomic-force microscopy for characterization of silicon, implated with heavy ions at high doses

Angelov, Christo; Groudev, P.; **Mikli, Valdek** Proceedings of 11th Conference "Materials for Information Tech. in the New Millenium" : ISCMP : Varna, 2001 2001 / p. 460-464

Valgustkiirgav räni

Krustok, Jüri Horisont 2001 / 1, lk. 12

Üliõhuke päikesepaneel avab energia tootmisele uued ukсед

Alvela, Ain; **Krautmann, Robert** novaator.err.ee 2023 [Üliõhuke päikesepaneel avab energia tootmisele uued ukсед](https://digikogu.taltech.ee/et/Item/e7e64926-5d49-40ad-8b3a-e225ea034f7d)
<https://digikogu.taltech.ee/et/Item/e7e64926-5d49-40ad-8b3a-e225ea034f7d> Ученый из Эстонии разрабатывает солнечные панели, которые изменят мир

Зависимость подвижности электронов и дырок от температуры и концентрации примеси в кремнии

Rang, Toomas; Velme, Enn Анализ и моделирование технических устройств и систем АСУТП 1977 / с. 115-120 : ил
https://www.ester.ee/record=b2190987*est <https://digikogu.taltech.ee/et/Item/b7c66054-0b4f-4684-9453-442bc7e6e200>

Изучение иммобилизации протеаз на кремнеземных материалах

Jegorov, H.R.; Kivisilla, Külliki; Kipper, Heino; Erin, Anne; Köstner, Ado Получение и применение иммобилизованных ферментов 1977 / с. 29-34 https://www.ester.ee/record=b1309558*est <https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73>

Иммобилизация пепсина на кремнеземных материалах

Lukoševiciene, N.; Sadauskas, P.; Ciurlis, T.; Kreen, Malle; Köstner, Ado Получение и применение иммобилизованных ферментов 1977 / с. 57-66 : илл https://www.ester.ee/record=b1309558*est <https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73>

Импульсно-плазменное легирование кремния сурьмой

Gavrilov, Aleksei; Katšurin, G.A. Электрофизические свойства полупроводниковых и диэлектрических материалов 1983 / с. 15-28 : ил https://www.ester.ee/record=b1291687*est <https://digikogu.taltech.ee/et/Item/9447de85-407e-426e-843d-2f0c98097f4e>

Импульсно-плазменный отжиг слоев кремния, имплантированных бором

Gavrilov, Aleksei; Katšurin, G.A. Электрофизические свойства полупроводниковых и диэлектрических материалов 1983 / с. 3-13 : ил https://www.ester.ee/record=b1291687*est <https://digikogu.taltech.ee/et/Item/9447de85-407e-426e-843d-2f0c98097f4e>

Инжекционные зависимости времени жизни неосновных носителей заряда в кремнии, легированном золотом и платиной

Udal, Andres Силовые быстродействующие полупроводниковые приборы : сборник статей. Часть II 1989 / с. 101-105 : ил., табл https://www.ester.ee/record=b1264433*est

Испульсное легирование кремния в сильноточном газовом разряде

Gavrilov, Aleksei; Katšurin, G.A. Письма в Журнал технической физики 1982 / с. 388-391 https://www.ester.ee/record=b2142356*est

Комплексное рентгенодифракционное исследование строения нарушенных слоев, обусловленных резкой кремнии

Milvidski, M.; Fomin, V.; Meiler, Boriss Физика и химия обработки материалов 1986 / с. 122-125
https://www.ester.ee/record=b1804847*est

Межфазное взаимодействие на контакте Ni-Si и Ni-GaAs

Meiler, Boriss Поверхность : физика, химия, механика 1985 / с. 62-67 : илл https://www.ester.ee/record=b2149829*est

Моделирование технологического процесса кремниевых силовых полупроводниковых приборов на ЭВМ

Rang, Toomas; Velme, Enn Синтез и диагностика цифровых устройств и систем 1982 / с. 107-112 : ил
https://www.ester.ee/record=b1328194*est <https://digikogu.taltech.ee/et/Item/febd586e-d7fa-4fbd-bf41-40576a75f94b>

Наращивание поликристаллических слоев кремния на рельефную поверхность двуокиси кремния

Paat, Aadu; Timma, Enn; Tromboveti, A. Труды по физике : сборник статей. 6 1973 / с. 27-33 : илл
https://www.ester.ee/record=b2190564*est <https://digikogu.taltech.ee/et/Item/020d3bce-d60f-45bd-aa8f-4906f2c1d0d6>

О работе таблеточных фоторезисторов в кремнийорганической жидкости

Valdna, Vello Физическая химия соединений AlIBVI 1981 / с. 27-34 : илл https://www.ester.ee/record=b1533413*est
<https://digikogu.taltech.ee/et/Item/dceb76ed-f60b-4ce9-b87e-618a41d25bb8>

О целесообразности увеличения обратного напряжения силовых кремниевых диодов

Vaher, G.; Tarma, Mati Применение эпитаксиальной технологии в производстве силовых полупроводниковых приборов : сборник материалов Всесоюзного научно-технического семинара. Часть 1 1978 / с. 21-24 : илл
https://www.ester.ee/record=b1273235*est

Об определении экологических ПДК для минеральных форм азота, фосфора и кремния в водных объектах

Säärekõnno, Jüri Tallinna Tehnikaülikooli Toimetised 1990 / lk. 32-36: ill

Определение механической растираемости неорганических носителей

Köstner, Ado; Kipper, Heino; Erin, Anne; Pedak, M. Получение и применение иммобилизованных ферментов 1977 / с. 51-55 : илл https://www.ester.ee/record=b1309558*est <https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73>

Отжиг имплантированных слоев кремния в плазме импульсного газового разряда

Gavrilov, Aleksei; Katšurin, G.A. Физика и техника полупроводников = Physics and technics of semiconductors 1981 / с.1232-1234 https://www.ester.ee/record=b1263919*est

Получение высокохромистых сплавов TiC-Fe-Cr, легированных кремнием

Kübarsepp, Jakob Порошковая металлургия = Powder metallurgy : ежемесячный научно-технический журнал 1986 / с. 65-69 : рис., таб https://www.ester.ee/record=b1645489*est

Получение иммобилизованной протеазы из Actinomyces vulgaris PA-II-4 и изучение некоторых ее свойств

Jegorov, H.R.; Erin, Anne; Köstner, Ado; Loginova, L.G.; Golovina, I.G. Получение и применение иммобилизованных ферментов 1977 / с. 35-41 : илл https://www.ester.ee/record=b1309558*est <https://digikogu.taltech.ee/et/Item/67557c4a-b3ad-4f67-9fe9-4590245ecb73>

Применение анодного окисления при исследовании электрофизических характеристик полупроводниковых структур "кремний на изоляторе"

Gavrilov, Aleksei Tallinna Tehnikaülikooli Toimetised 1990 / lk. 53-59: ill

Скорость связывания кремнезема песка в случае образования высоковольтных гидросиликатов кальция

Reiman, Värdi Сборник трудов (НИПИ силикатобетон) 1969 / с. [?] https://www.ester.ee/record=b1764431*est

Структура и глубина нарушенного слоя при грубой абразивной обработке монокристаллического кремния

Meiler, Boriss; Hatskevits, M.; Ladotškin, A.; Fomin, V. Tallinna Tehnikaülikooli Toimetised 1990 / lk. 60-71: ill

Термообработка пластин кремния с нарушенным слоем

Meiler, Boriss; Ladotškin, A.; Fomin, V. Tallinna Tehnikaülikooli Toimetised 1990 / lk. 72-86: ill

Численное моделирование процесса выключения одномерных кремниевых тиристорных структур

Velme, Enn; Udal, Andres Полупроводниковые приборы : сборник статей 1982 / с. 74-79 : ил
https://www.ester.ee/record=b1356516*est

Численное моделирование статических неизотермических процессов в кремниевых силовых диодных и тиристорных структурах в открытом состоянии

Velmre, Enn; Udal, Andres; Freidin, Boris Всесоюзный научно-технический семинар "Повышение параметров силовых полупроводниковых приборов на основе новых конструктивных решений и методов изготовления" (Запорожье, 1981) 1981 / с.37-38

Численное моделирование температурных распределений в кремниевых силовых полупроводниковых приборах при воздействии мощного импульса прямого тока

Velmre, Enn; Nurste, Ivar; Freidin, Boris Проблемы моделирования полупроводниковых структур и сложных схем на ЭВМ 1982 / с. 49-58 : ил https://www.ester.ee/record=b1339926*est <https://www.etera.ee/zoom/121726/view?page=3&p=separate&search=true&tool=search>

Численное моделирование физических процессов в одномерных кремниевых диодных структурах в стационарном режиме

Velmre, Enn; Freidin, Boris; Udal, Andres Алгоритмы и программы : информационный бюллетень 1980 / с. 88